

## Preliminary Data

### SIPMOS® Power Transistor

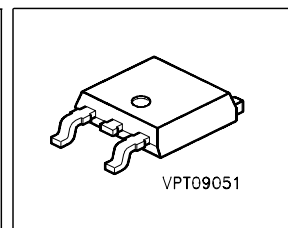
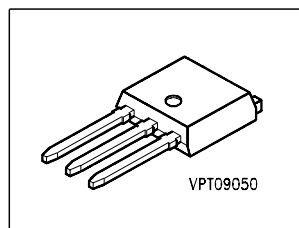
### SPD 10N10

#### Features

- N channel
- Enhancement mode
- Avalanche rated
- $dv/dt$  rated

#### Product Summary

|                                  |              |     |          |
|----------------------------------|--------------|-----|----------|
| Drain source voltage             | $V_{DS}$     | 100 | V        |
| Drain-Source on-state resistance | $R_{DS(on)}$ | 0.2 | $\Omega$ |
| Continuous drain current         | $I_D$        | 10  | A        |



| Type     | Package | Ordering Code   | Packaging     | Pin 1 | Pin 2 | Pin 3 |
|----------|---------|-----------------|---------------|-------|-------|-------|
| SPD10N10 | P-TO252 | Q67040-S4119-A2 | Tape and Reel | G     | D     | S     |
| SPU10N10 | P-TO251 | Q67040-S4111-A2 | Tube          |       |       |       |

#### Maximum Ratings, at $T_j = 25^\circ\text{C}$ , unless otherwise specified

| Parameter                                                                        | Symbol         | Value       | Unit              |
|----------------------------------------------------------------------------------|----------------|-------------|-------------------|
| Continuous drain current                                                         | $I_D$          | 10          | A                 |
| $T_C = 25^\circ\text{C}$                                                         |                | 6.3         |                   |
| $T_C = 100^\circ\text{C}$                                                        |                |             |                   |
| Pulsed drain current                                                             | $I_{Dpulse}$   | 40          |                   |
| $T_C = 25^\circ\text{C}$                                                         |                |             |                   |
| Avalanche energy, single pulse                                                   | $E_{AS}$       | 59          | mJ                |
| $I_D = 10\text{ A}$ , $V_{DD} = 25\text{ V}$ , $R_{GS} = 25\ \Omega$             |                |             |                   |
| Avalanche energy, periodic limited by $T_{jmax}$                                 | $E_{AR}$       | 4           |                   |
| Reverse diode $dv/dt$                                                            | $dv/dt$        | 6           | kV/ $\mu\text{s}$ |
| $I_S = 10\text{ A}$ , $V_{DS} = 0\text{ V}$ , $di/dt = 200\text{ A}/\mu\text{s}$ |                |             |                   |
| Gate source voltage                                                              | $V_{GS}$       | $\pm 20$    | V                 |
| Power dissipation                                                                | $P_{tot}$      | 40          | W                 |
| $T_C = 25^\circ\text{C}$                                                         |                |             |                   |
| Operating and storage temperature                                                | $T_j, T_{stg}$ | -55... +175 | $^\circ\text{C}$  |
| IEC climatic category; DIN IEC 68-1                                              |                | 55/150/56   |                   |

## Thermal Characteristics

| Parameter                                      | Symbol     | Values |      |      | Unit |
|------------------------------------------------|------------|--------|------|------|------|
|                                                |            | min.   | typ. | max. |      |
| Characteristics                                |            |        |      |      |      |
| Thermal resistance, junction - case            | $R_{thJC}$ | -      |      | 3.1  | K/W  |
| Thermal resistance, junction - ambient, leded  | $R_{thJA}$ | -      | -    | 100  |      |
| SMD version, device on PCB:                    | $R_{thJA}$ |        |      |      |      |
| @ min. footprint                               |            | -      | -    | 75   |      |
| @ 6 cm <sup>2</sup> cooling area <sup>1)</sup> |            | -      | -    | 50   |      |

## Electrical Characteristics, at $T_j = 25^\circ\text{C}$ , unless otherwise specified

| Parameter                                                                                                                                                                                                        | Symbol        | Values |          |          | Unit          |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------|--------|----------|----------|---------------|
|                                                                                                                                                                                                                  |               | min.   | typ.     | max.     |               |
| Static Characteristics                                                                                                                                                                                           |               |        |          |          |               |
| Drain- source breakdown voltage<br>$V_{GS} = 0\text{ V}$ , $I_D = 0.25\text{ mA}$                                                                                                                                | $V_{(BR)DSS}$ | 100    | -        | -        | V             |
| Gate threshold voltage, $V_{GS} = V_{DS}$<br>$I_D = 1\text{ mA}$                                                                                                                                                 | $V_{GS(th)}$  | 2.1    | 3        | 4        |               |
| Zero gate voltage drain current<br>$V_{DS} = 100\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_j = 25\text{ }^{\circ}\text{C}$<br>$V_{DS} = 100\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_j = 125\text{ }^{\circ}\text{C}$ | $I_{DSS}$     | -<br>- | 0.1<br>- | 1<br>100 | $\mu\text{A}$ |
| Gate-source leakage current<br>$V_{GS} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$                                                                                                                                    | $I_{GSS}$     | -      | 10       | 100      | nA            |
| Drain-Source on-state resistance<br>$V_{GS} = 10\text{ V}$ , $I_D = 6\text{ A}$                                                                                                                                  | $R_{DS(on)}$  | -      | 0.15     | 0.2      | $\Omega$      |

<sup>1)</sup> Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical without blown air.

**Electrical Characteristics**, at  $T_j = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

| Parameter                                                                                                                 | Symbol       | Values |      |      | Unit |
|---------------------------------------------------------------------------------------------------------------------------|--------------|--------|------|------|------|
|                                                                                                                           |              | min.   | typ. | max. |      |
| Dynamic Characteristics                                                                                                   |              |        |      |      |      |
| Transconductance<br>$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 6\text{ A}$                                    | $g_{fs}$     | 3      | 4.3  | -    | S    |
| Input capacitance<br>$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$                                  | $C_{iss}$    | -      | 400  | 530  | pF   |
| Output capacitance<br>$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$                                 | $C_{oss}$    | -      | 125  | 180  |      |
| Reverse transfer capacitance<br>$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$                       | $C_{rss}$    | -      | 70   | 105  |      |
| Turn-on delay time<br>$V_{DD} = 30\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 3\text{ A}$ ,<br>$R_G = 50\text{ }\Omega$  | $t_{d(on)}$  | -      | 10   | 15   | ns   |
| Rise time<br>$V_{DD} = 30\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 3\text{ A}$ ,<br>$R_G = 50\text{ }\Omega$           | $t_r$        | -      | 45   | 70   |      |
| Turn-off delay time<br>$V_{DD} = 30\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 3\text{ A}$ ,<br>$R_G = 50\text{ }\Omega$ | $t_{d(off)}$ | -      | 55   | 75   |      |
| Fall time<br>$V_{DD} = 30\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 3\text{ A}$ ,<br>$R_G = 50\text{ }\Omega$           | $t_f$        | -      | 40   | 55   |      |

**Electrical Characteristics**, at  $T_j = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

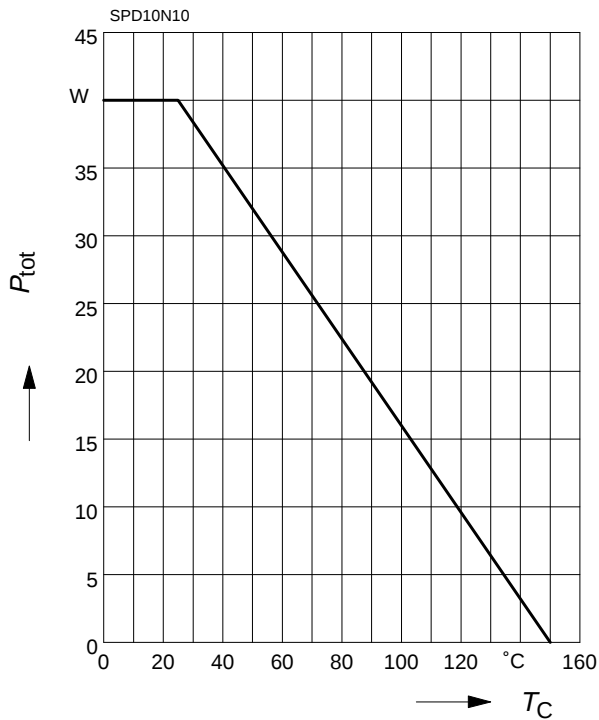
| Parameter                                                                                              | Symbol                 | Values |      |      | Unit |
|--------------------------------------------------------------------------------------------------------|------------------------|--------|------|------|------|
|                                                                                                        |                        | min.   | typ. | max. |      |
| Dynamic Characteristics                                                                                |                        |        |      |      |      |
| Gate to source charge<br>$V_{DD} = 80\text{ V}$ , $I_D = 10\text{ A}$                                  | $Q_{gs}$               | -      | 4.5  | 7    | nC   |
| Gate to drain charge<br>$V_{DD} = 80\text{ V}$ , $I_D = 10\text{ A}$                                   | $Q_{gd}$               | -      | 29.6 | 45   |      |
| Gate charge total<br>$V_{DD} = 80\text{ V}$ , $I_D = 10\text{ A}$ , $V_{GS} = 0\text{ to }10\text{ V}$ | $Q_g$                  | -      | 46   | 69   |      |
| Gate plateau voltage<br>$V_{DD} = 80\text{ V}$ , $I_D = 10\text{ A}$                                   | $V_{(\text{plateau})}$ | -      | 6.8  | -    | V    |

**Reverse Diode**

|                                                                                                     |          |   |     |      |               |
|-----------------------------------------------------------------------------------------------------|----------|---|-----|------|---------------|
| Inverse diode continuous forward current<br>$T_C = 25\text{ }^{\circ}\text{C}$                      | $I_S$    | - | -   | 10   | A             |
| Inverse diode direct current,pulsed<br>$T_C = 25\text{ }^{\circ}\text{C}$                           | $I_{SM}$ | - | -   | 40   |               |
| Inverse diode forward voltage<br>$V_{GS} = 0\text{ V}$ , $I_F = 20\text{ A}$                        | $V_{SD}$ | - | 1.4 | 1.6  | V             |
| Reverse recovery time<br>$V_R = 30\text{ V}$ , $I_F = I_S$ , $di_F/dt = 100\text{ A}/\mu\text{s}$   | $t_{rr}$ | - | 170 | 255  | ns            |
| Reverse recovery charge<br>$V_R = 30\text{ V}$ , $I_F = I_S$ , $di_F/dt = 100\text{ A}/\mu\text{s}$ | $Q_{rr}$ | - | 0.3 | 0.45 | $\mu\text{C}$ |

### Power Dissipation

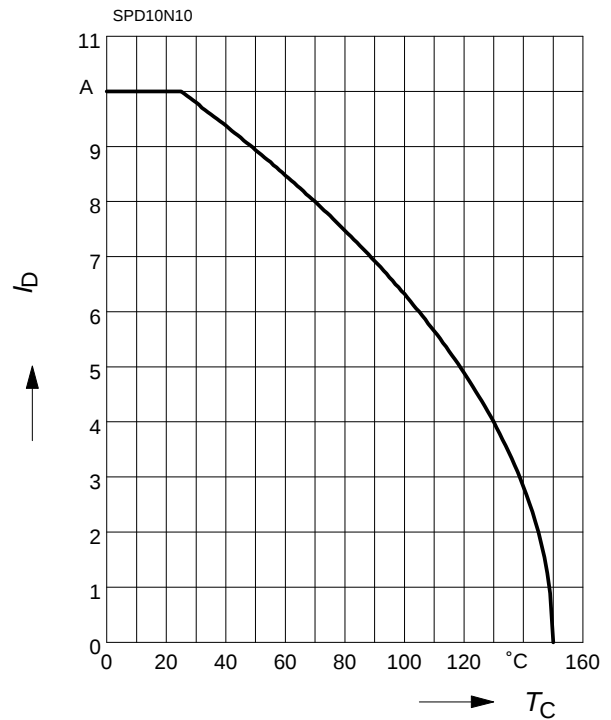
$$P_{\text{tot}} = f(T_C)$$



### Drain current

$$I_D = f(T_C)$$

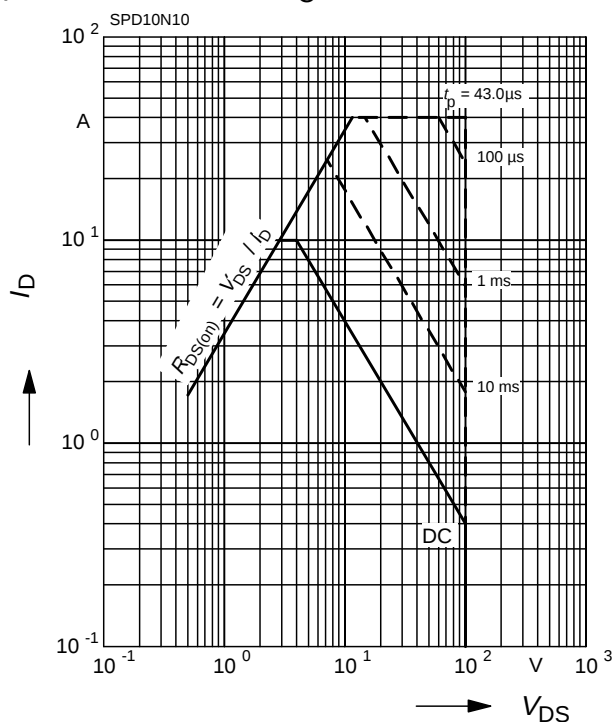
parameter:  $V_{GS} \geq 10 \text{ V}$



### Safe operating area

$$I_D = f(V_{DS})$$

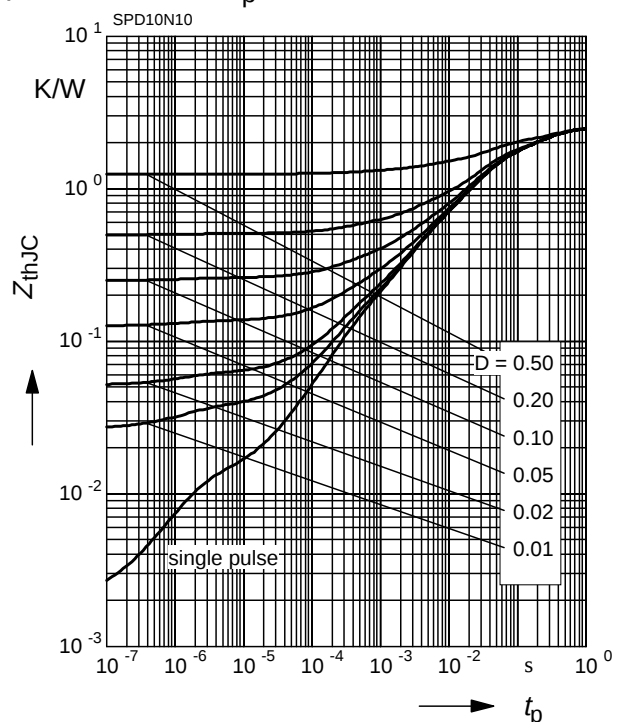
parameter:  $D = 0$ ,  $T_C = 25^{\circ}\text{C}$



### Transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

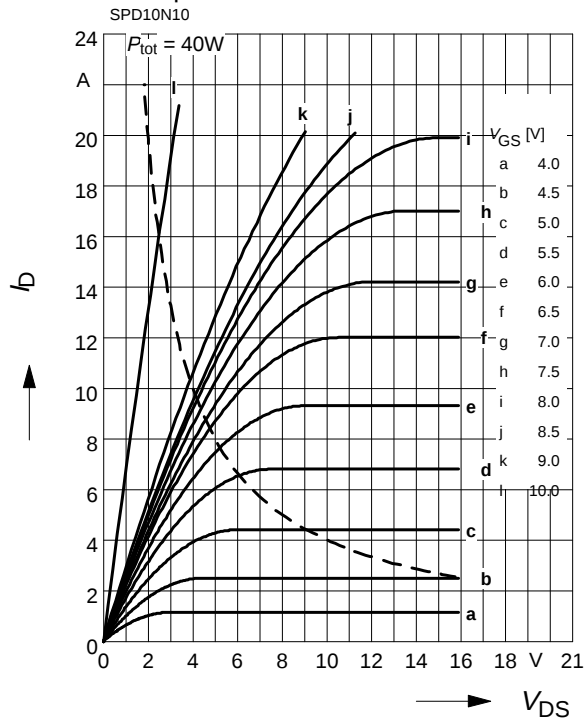
parameter:  $D = t_p / T$



**Typ. output characteristics**

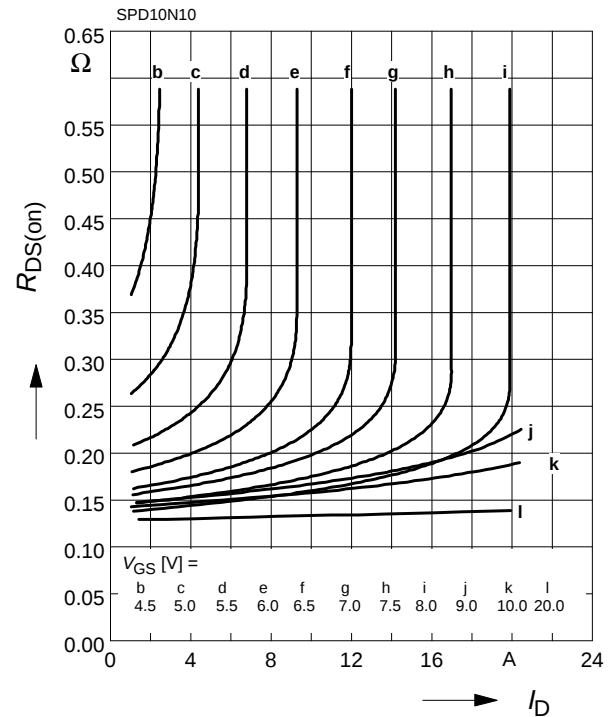
$$I_D = f(V_{DS})$$

parameter:  $t_p = 80 \mu s$


**Typ. drain-source-on-resistance**

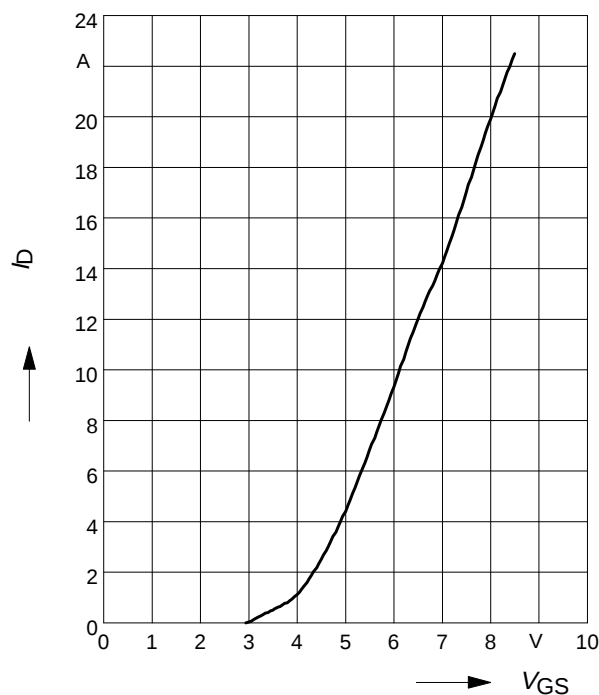
$$R_{DS(on)} = f(I_D)$$

parameter:  $V_{GS}$


**Typ. transfer characteristics  $I_D = f(V_{GS})$** 

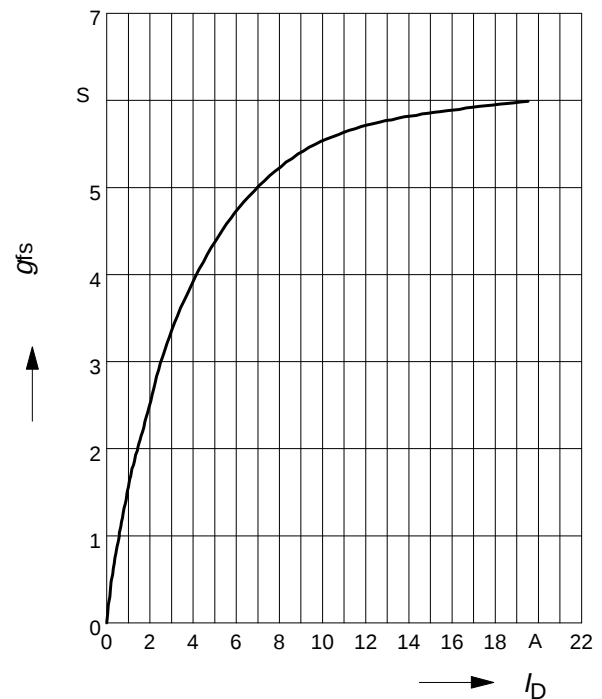
parameter:  $t_p = 80 \mu s$

$$V_{DS} \geq 2 \times I_D \times R_{DS(on)} \max$$


**Typ. forward transconductance**

$$g_{fs} = f(I_D); T_j = 25^\circ C$$

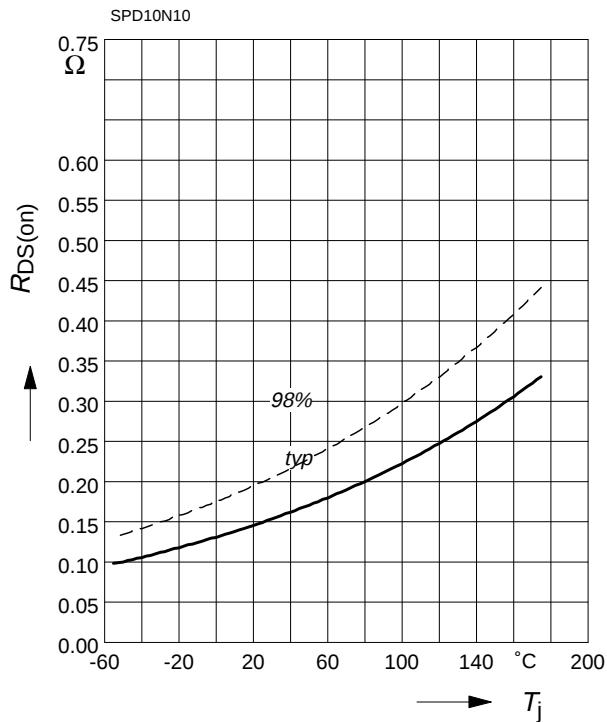
parameter:  $g_{fs}$



### Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

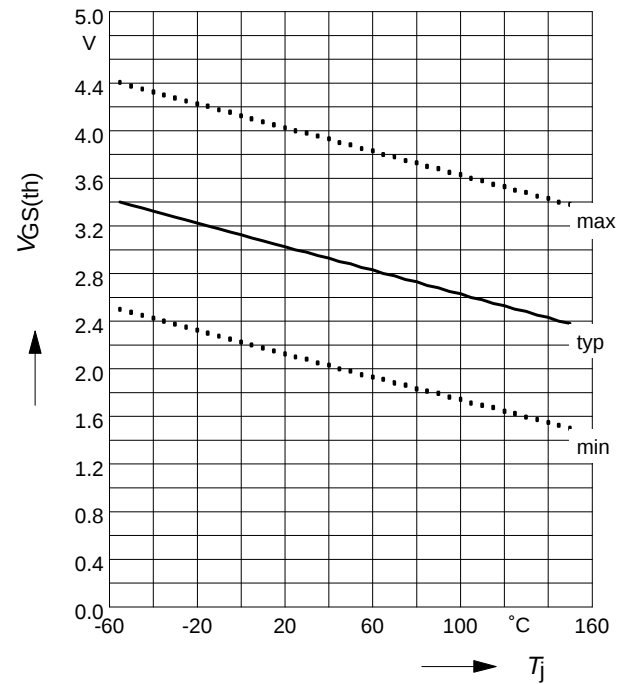
parameter :  $I_D = 6\text{ A}$ ,  $V_{GS} = 10\text{ V}$



### Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

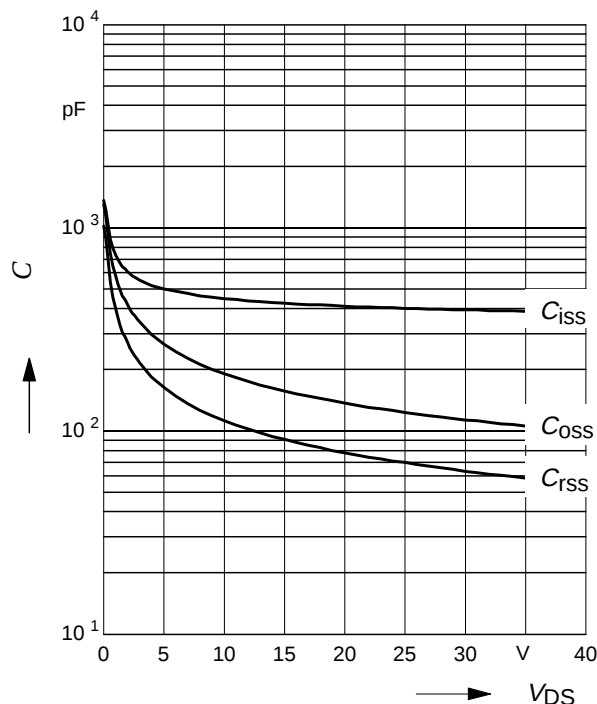
parameter :  $V_{GS} = V_{DS}$ ,  $I_D = 1\text{ mA}$



### Typ. capacitances

$$C = f(V_{DS})$$

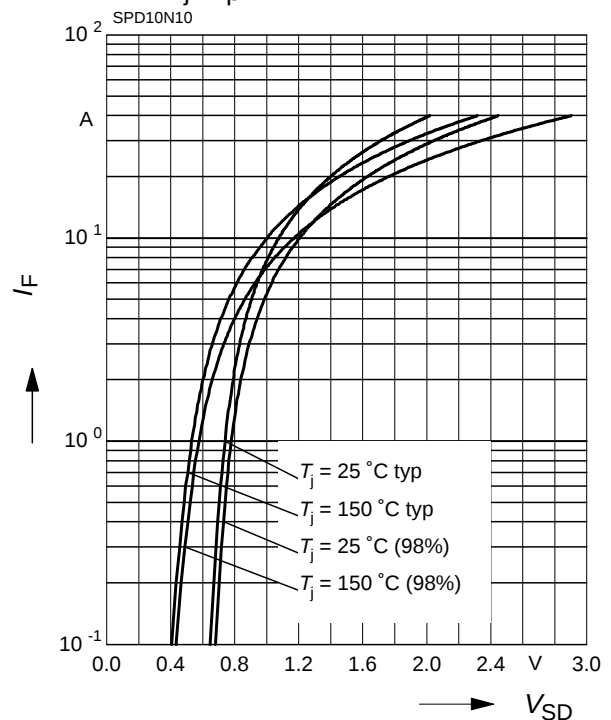
parameter:  $V_{GS} = 0\text{ V}$ ,  $f = 1\text{ MHz}$



### Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

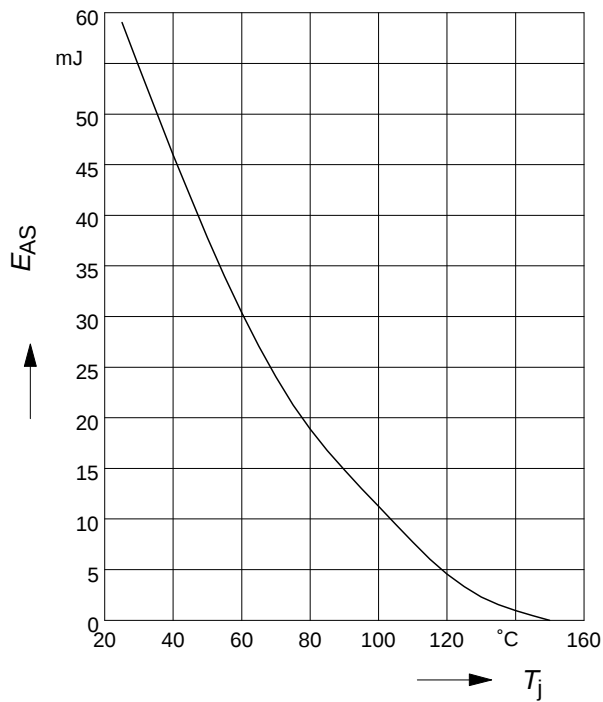
parameter:  $T_j$ ,  $t_p = 80\text{ }\mu\text{s}$



**Avalanche Energy  $E_{AS} = f(T_j)$** 

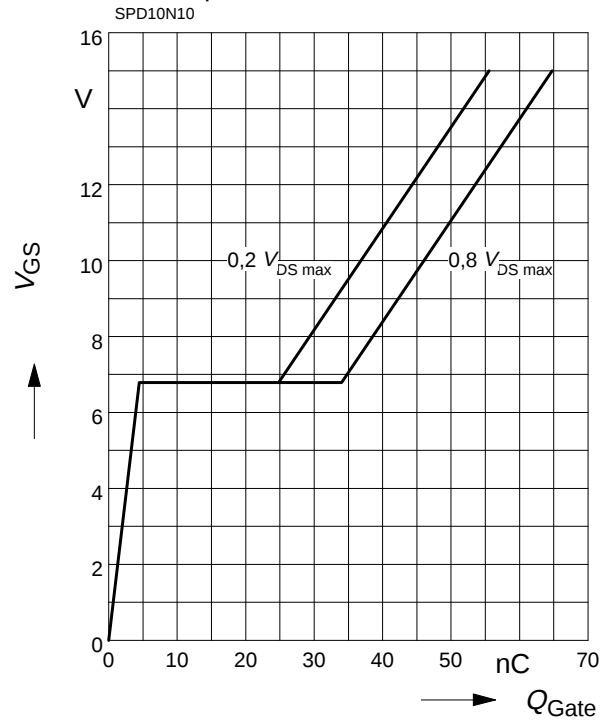
parameter:  $I_D = 10\text{ A}$ ,  $V_{DD} = 25\text{ V}$

$R_{GS} = 25\ \Omega$


**Typ. gate charge**

$V_{GS} = f(Q_{Gate})$

parameter:  $I_{D\text{ puls}} = 10\text{ A}$


**Drain-source breakdown voltage**

$V_{(BR)DSS} = f(T_j)$

